

## N-Channel 60-V (D-S) MOSFET

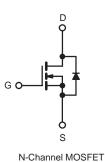
PRODU	CT SUMMARY	
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)
60	0.029 at V <sub>GS</sub> = 10 V	7.0
60	0.033 at V <sub>GS</sub> = 4.5 V	5.6

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC







Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		$V_{DS}$		60	V
Gate-Source Voltage		$V_{GS}$	± 20		
Continuous Drain Current (T <sub>.I</sub> = 175 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	7.0	6.0	A
Continuous Drain Current (1 j = 175°C)	T <sub>A</sub> = 70 °C		6.1	5.0	
Pulsed Drain Current		I <sub>DM</sub>	40		A
Avalanche Current		I <sub>AS</sub>	15		
Single Pulse Avalanche Energy		E <sub>AS</sub>		11	mJ
Mariana Barra Birainatian	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.3	1.7	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	' D	2.3	1.2	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55	to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	R <sub>thJA</sub>	36	45	
Maximum Junction-to-Ambient	Steady State		75	90	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	17	20	

#### Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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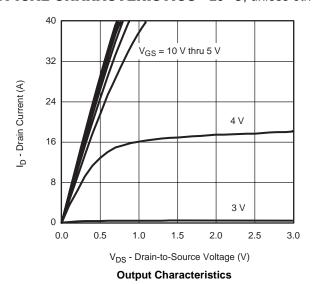


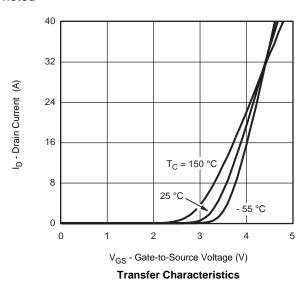
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1		3	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zoro Gato Voltago Drain Current	I <sub>DSS</sub>	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	<sub>OS</sub> = 60 V, V <sub>GS</sub> = 0 V		1	μΑ	
Zero Gate Voltage Drain Current		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$	= 55 °C		20		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
		$V_{GS} = 10 \text{ V}, I_D = 6.0 \text{ A}$		0.028		Ω	
	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 6.0 \text{ A}, T_J = 125 \text{ °C}$		0.032			
Drain-Source On-State Resistance <sup>a</sup>		$V_{GS} = 10 \text{ V}, I_D = 6.0 \text{ A}, T_J = 175 ^{\circ}\text{C}$		0.040			
	•	$V_{GS} = 4.5 \text{ V}, I_D = 5.1 \text{ A}$		0.033			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_D = 6.0 \text{ A}$		25		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 1.7 A, V <sub>GS</sub> = 0 V		0.8	1.2	V	
Dynamic <sup>b</sup>			•				
Total Gate Charge	$Q_g$			18	27		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 6.0 \text{ A}$		3.4		nC	
Gate-Drain Charge	$Q_{gd}$			5.3			
Gate Resistance	$R_g$	V <sub>GS</sub> = 0.1 V, f = 5 MHz	0.5	1.4	2.4	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			10	20		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 30 V, $R_L$ = 30 $\Omega$		10	20		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 1 A, $V_{GEN}$ = 10 V, $R_g$ = 6 $\Omega$		25	50	ns	
Fall Time	t <sub>f</sub>			12	24		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.7 A, dI/dt = 100 A/μs		50	80		

#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

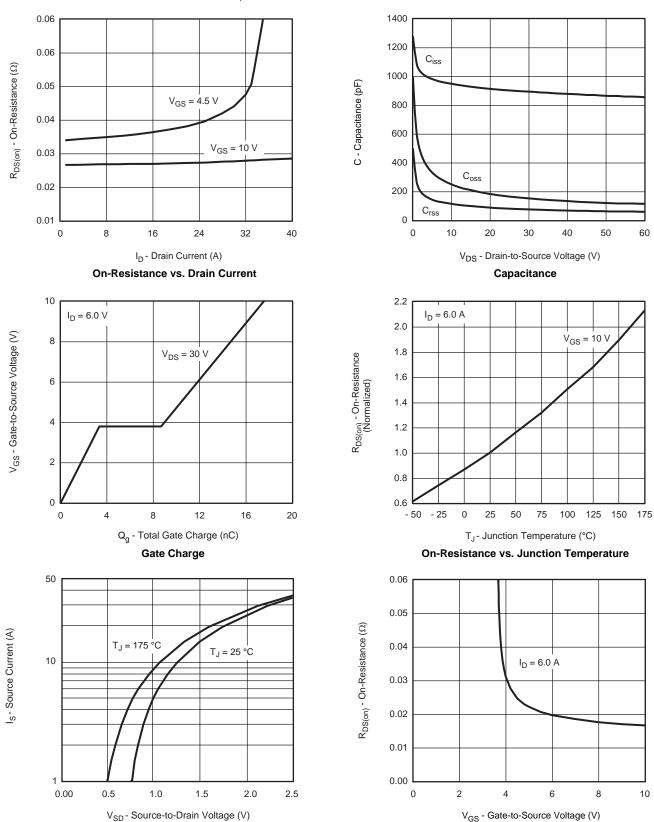




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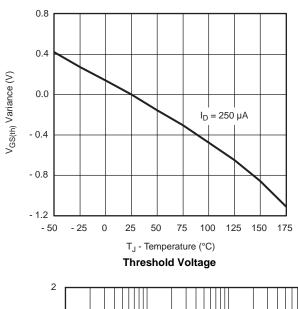
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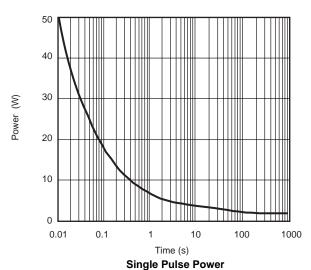
On-Resistance vs. Gate-to-Source Voltage

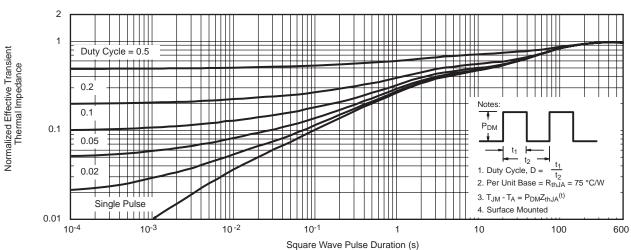
Source-Drain Diode Forward Voltage

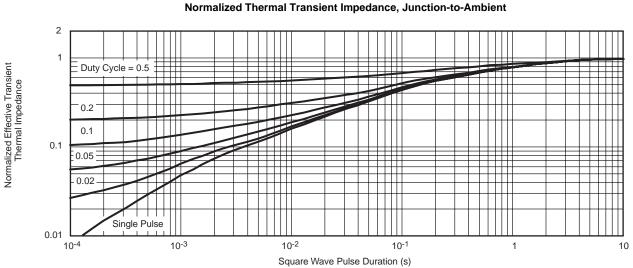


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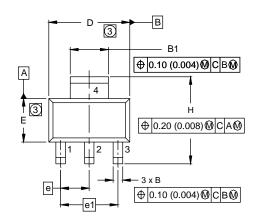


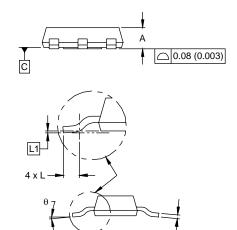
Normalized Thermal Transient Impedance, Junction-to-Foot

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## **SOT-223 (HIGH VOLTAGE)**





DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
Α	1.55	1.80	0.061	0.071
В	0.65	0.85	0.026	0.033
B1	2.95	3.15	0.116	0.124
С	0.25	0.35	0.010	0.014
D	6.30	6.70	0.248	0.264
E	3.30	3.70	0.130	0.146
е	2.30 BSC		0.0905 BSC	
e1	4.60 BSC		0.181	BSC
Н	6.71	7.29	0.264	0.287
L	0.91	-	0.036	-
L1	0.061 BSC		0.0024	4 BSC
θ	-	10'	-	10'

ECN: S-82109-Rev. A, 15-Sep-08

DWG: 5969

#### Notes

- 1. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 2. Dimensions are shown in millimeters (inches).
- 3. Dimension do not include mold flash.
- 4. Outline conforms to JEDEC outline TO-261AA.

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